

$<\!$ 0.5 Ω CMOS 1.65 V to 3.6 V Quad SPST Switches

ADG811/ADG812/ADG813

FEATURES

0.5 Ω typ on resistance 0.8 Ω max on resistance at 125°C 1.65 V to 3.6 V operation Automotive temperature range: -40°C to +125°C High current carrying capability: 300 mA continuous Rail-to-rail switching operation Fast switching times: <25 ns Typical power consumption < 0.1 μ W

APPLICATIONS

Cellular phones MP3 players Power routing Battery-powered systems PCMCIA cards Modems Audio and video signal routing Communications systems

GENERAL DESCRIPTION

The ADG811, ADG812, and ADG813 are low voltage CMOS devices containing four independently selectable switches. These switches offer ultralow on resistance of less than 0.8 Ω over the full temperature range. The digital inputs can handle 1.8 V logic with a 2.7 V to 3.6 V supply.

These devices contain four independent single-pole/singlethrow (SPST) switches. The ADG811 and ADG812 differ only in that the digital control logic is inverted. The ADG811 switches are turned on with a logic low on the appropriate control input, while a logic high is required to turn on the switches of the ADG812. The ADG813 contains two switches whose digital control logic is similar to the ADG811, while the logic is inverted on the other two switches.

Each switch conducts equally well in both directions when on and has an input signal range that extends to the supplies. The ADG813 exhibits break-before-make switching action.

The ADG811, ADG812, and ADG813 are fully specified for 3.3 V, 2.5 V, and 1.8 V supply operation. They are available in a 16-lead TSSOP package.

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FUNCTIONAL BLOCK DIAGRAMS

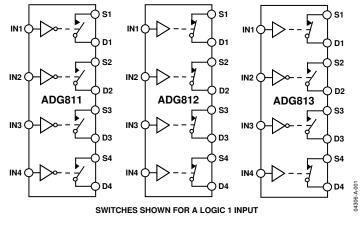


Figure 1.

PRODUCT HIGHLIGHTS

- 1. <0.8 Ω over full temperature range of -40°C to +125°C.
- 2. Single 1.65 V to 3.6 V operation.
- 3. Operational with 1.8 V CMOS logic.
- 4. High current handling capability (300 mA continuous current at 3.3 V).
- 5. Low THD+N (0.02% typ).

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ADG811/ADG812/ADG813—SPECIFICATIONS

Table 1. V_{DD} = 2.7 V to 3.6 V, GND = 0 V, unless otherwise noted¹

Parameter	+25°C	–40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 V to V _{DD}	V	
On Resistance (R _{ON})	0.5			Ωtyp	$V_{\text{DD}} = 2.7 \text{ V}, V_{\text{S}} = 0 \text{ V} \text{ to } V_{\text{DD}}, I_{\text{S}} = 10 \text{ mA}$
	0.65	0.75	0.8	Ωmax	Figure 18
On Resistance Match between	0.04			Ωtyp	$V_{DD} = 2.7 \text{ V}, \text{ V}_{\text{S}} = 0.5 \text{ V}, \text{ I}_{\text{S}} = 10 \text{ mA}$
Channels (ΔR_{ON})		0.075	0.08	Ωmax	
On Resistance Flatness (R _{FLAT(ON)})	0.1			Ωtyp	$V_{DD} = 2.7 \text{ V}, \text{ V}_{\text{S}} = 0 \text{ V} \text{ to } \text{V}_{\text{DD}}, \text{ I}_{\text{S}} = 10 \text{ mA}$
		0.15	0.16	Ωmax	
LEAKAGE CURRENTS					$V_{DD} = 3.6 V$
Source Off Leakage Is (OFF)	±0.2			nA typ	$V_{s} = 0.6 \text{ V}/3.3 \text{ V}, V_{D} = 3.3 \text{ V}/0.6 \text{ V};$
	±1	±8	±80	nA max	Figure 19
Drain Off Leakage I _D (OFF)	±0.2			nA typ	$V_{s} = 0.6 \text{ V}/3.3 \text{ V}, V_{D} = 3.3 \text{ V}/0.6 \text{ V};$
	±1	±8	±80	nA max	Figure 19
Channel On Leakage I _D , I _S (ON)	±0.2			nA typ	$V_{s} = V_{D} = 0.6 V \text{ or } 3.3 V;$ Figure 20
	±1	±15	±90	nA max	
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2	V min	
Input Low Voltage, VINL			0.8	V max	
Input Current, InL or InH	0.005			μA typ	$V_{IN} = V_{INL} \text{ or } V_{INH}$
			±0.1	µA max	
C _{IN} , Digital Input Capacitance	6			pF typ	
DYNAMIC CHARACTERISTICS ²					
t _{on}	21			ns typ	$R_L = 50 \Omega, C_L = 35 pF$
	25	26	28	ns max	V _s = 1.5 V/0 V; Figure 21
t _{OFF}	4			ns typ	$R_L = 50 \Omega, C_L = 35 pF$
	5	6	7	ns max	V _s = 1.5 V; Figure 21
Break-Before-Make Time Delay (t _{BBM})	17			ns typ	$R_L = 50 \Omega, C_L = 35 pF$
(ADG813 only)			5	ns min	$V_{s1} = V_{s2} = 1.5 V$; Figure 22
Charge Injection	30			pC typ	$V_s = 1.5 V, R_s = 0 \Omega, C_L = 1 nF;$
Off Isolation	67			d D turn	Figure 23 R _L = 50 Ω, C _L = 5 pF, f = 100 kHz;
Offisolation	-67			dB typ	$R_L = 50.02$, $C_L = 5 \text{ pr}$, $T = 100 \text{ km2}$; Figure 24
Channel-to-Channel Crosstalk	-90			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$;
					Figure 26
Total Harmonic Distortion (THD + N)	0.02			%	$R_L = 32 \Omega$, f = 20 Hz to 20 kHz, V _s = 2 V p-p
Insertion Loss	-0.05			dB typ	$R_L = 50 \Omega, C_L = 5 \text{ pF}, f = 100 \text{ kHz}$
–3 dB Bandwidth	90			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; Figure 25
C _s (OFF)	30			pF typ	,,
C _D (OFF)	35			pF typ	
$C_D, C_S (ON)$	60			pF typ	
POWER REQUIREMENTS				F: 78	V _{DD} = 3.6 V
IDD	0.003			μA typ	Digital inputs = 0 V or 3.6 V
-00	0.000	1.0	4	μA max	

¹Temperature range for the Y version is -40° C to $+125^{\circ}$ C.

²Guaranteed by design, not subject to production test.

Parameter	+25°C	–40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$0 V$ to V_{DD}	V	
On Resistance (R _{ON})	0.65			Ωtyp	$V_{DD} = 2.3 \text{ V}, \text{ V}_{\text{S}} = 0 \text{ V}$ to $V_{DD}, \text{ I}_{\text{S}} = 10 \text{ mA}$
	0.72	0.8	0.88	Ωmax	Figure 18
On Resistance Match between	0.04			Ωtyp	$V_{DD} = 2.3 \text{ V}; \text{ V}_{\text{S}} = 0.55 \text{ V}, \text{ I}_{\text{S}} = 10 \text{ mA}$
Channels (ΔR_{ON})		0.08	0.085	Ωmax	
On Resistance Flatness (R _{FLAT(ON)})	0.16			Ωtyp	$V_{DD} = 2.3 \text{ V}; \text{ V}_{\text{S}} = 0 \text{ V} \text{ to } \text{V}_{\text{DD}}, \text{ I}_{\text{S}} = 10 \text{ mA}$
		0.23	0.24	Ωmax	
LEAKAGE CURRENTS					$V_{DD} = 2.7 V$
Source Off Leakage Is (OFF)	±0.2			nA typ	$V_{s} = 0.6 V/2.4 V, V_{D} = 2.4 V/0.6 V;$
	±1	±6	±35	nA max	Figure 19
Drain Off Leakage I _D (OFF)	±0.2			nA typ	$V_{\rm S} = 0.6 \text{ V}/2.4 \text{ V}, V_{\rm D} = 2.4 \text{ V}/0.6 \text{ V};$
	±1	±6	±35	nA max	Figure 19
Channel On Leakage I _D , I _S (ON)	±0.2			nA typ	$V_{s} = V_{D} = 0.6$ V or 2.4 V; Figure 20
-	±1	±11	±70	nA max	_
DIGITAL INPUTS					
Input High Voltage, V _{INH}			1.7	V min	
Input Low Voltage, V _{INL}			0.7	V max	
	0.005			μA typ	$V_{IN} = V_{INL} \text{ or } V_{INH}$
			±0.1	µA max	
C _{IN} , Digital Input Capacitance	6			pF typ	
DYNAMIC CHARACTERISTICS ²				. ,.	
t _{on}	22			ns typ	$R_L = 50 \Omega, C_L = 35 pF$
	27	29	30	ns max	Vs = 1.5 V/ 0 V; Figure 21
t _{OFF}	4			ns typ	$R_L = 50 \Omega, C_L = 35 pF$
	6	7	8	ns max	Vs = 1.5 V; Figure 21
Break-Before-Make Time Delay (t _{BBM})	18			ns typ	$R_L = 50 \Omega, C_L = 35 pF$
(ADG813 only)			5	ns min	$V_{s1} = V_{s2} = 1.5 V$; Figure 22
Charge Injection	25			pC typ	$V_{s} = 1.25 V, R_{s} = 0 \Omega, C_{L} = 1 nF;$
5,					Figure 23
Off Isolation	-67			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; Figure 24
Channel-to-Channel Crosstalk	-90			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, f = 100 kHz; Figure 26
Total Harmonic Distortion (THD + N)	0.022			%	$R_L = 32 \Omega$, f = 20 Hz to 20 kHz, V _s = 1.5 V p-p
Insertion Loss	-0.06			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$
–3 dB Bandwidth	90			MHz typ	$R_L = 50 \Omega_2$, $C_L = 5 pF$; Figure 25
Cs (OFF)	32			pF typ	
C _D (OFF)	37			pF typ	
C_D , C_S (ON)	60			pF typ	
POWER REQUIREMENTS				P' 9P	V _{DD} = 2.7 V
	0.003			μA typ	$v_{DD} = 2.7 v$ Digital inputs = 0 V or 2.7 V
DD	0.005	1.0	4	μΑ typ μΑ max	
		1.0	4	µл шах	

Table 2. V_{DD} = 2.5 V ± 0.2 V, GND = 0 V, unless otherwise noted¹

 1 Temperature range for the Y version is –40°C to +125°C. 2 Guaranteed by design, not subject to production test.

Parameter	+25°C	–40°C to +85°C	–40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 V to V _{DD}	V	
On Resistance (R _{ON})	1			Ωtyp	$V_{DD} = 1.8 V, V_S = 0 V to V_{DD}, I_S = 10 mA;$
	1.4	2.2	2.2	Ωmax	Figure 18
	2.5	4	4	Ωmax	$V_{DD} = 1.65 \text{ V}, \text{ V}_{\text{S}} = 0 \text{ V} \text{ to } \text{ V}_{DD}, \text{ I}_{\text{S}} = 10 \text{ mA}$
On Resistance Match between Channels (ΔR_{ON})	0.1			Ωtyp	$V_{\text{DD}} = 1.65 \text{ V}, V_{\text{S}} = 0.7 \text{ V}, I_{\text{S}} = 10 \text{ mA}$
LEAKAGE CURRENTS					$V_{DD} = 1.95 V$
Source Off Leakage Is (OFF)	±0.2			nA typ	$V_{s} = 0.6 \text{ V}/1.65 \text{ V}, V_{D} = 1.65 \text{ V}/0.6 \text{ V};$
	±1	±5	±30	nA max	Figure 19
Drain Off Leakage I _D (OFF)	±0.2			nA typ	$V_{S} = 0.6 \text{ V}/1.65 \text{ V}, V_{D} = 1.65 \text{ V}/0.6 \text{ V};$
	±1	±5	±30	nA max	Figure 19
Channel On Leakage I _D , Is (ON)	±0.2			nA typ	$V_{s} = V_{D} = 0.6 V \text{ or } 1.65 V;$ Figure 20
	±1	±9	±60	nA max	
DIGITAL INPUTS					
Input High Voltage, V _{INH}			0.65V _{DD}	V min	
Input Low Voltage, VINL			0.35V _{DD}	V max	
Input Current, I _{INL} or I _{INH}	0.005			μA typ	$V_{IN} = V_{INL} \text{ or } V_{INH}$
			±0.1	μA max	
CIN, Digital Input Capacitance	6			pF typ	
DYNAMIC CHARACTERISTICS ²					
ton	27			ns typ	$R_L = 50 \Omega, C_L = 35 pF$
	35	36	37	ns max	V _s = 1.5 V/ 0 V; Figure 21
toff	6			ns typ	$R_L = 50 \Omega, C_L = 35 pF$
	8	9	10	ns max	V _s = 1.5 V; Figure 21
Break-Before-Make Time Delay (t _{BBM})	20			ns typ	$R_L = 50 \Omega, C_L = 35 pF$
(ADG813 only)			5	ns min	$V_{s1} = V_{s2} = 1$ V; Figure 22
Charge Injection	15			pC typ	$V_s = 1 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; Figure 23
Off Isolation	-67			dB typ	R_L = 50 Ω, C_L = 5 pF, f = 100 kHz; Figure 24
Channel-to-Channel Crosstalk	-90			dB typ	R _L = 50 Ω, C _L = 5 pF, f = 100 kHz; Figure 26
Total Harmonic Distortion (THD + N)	0.14			%	R_L = 32 Ω, f = 20 Hz to 20 kHz, V _s = 1.2 V p-p
Insertion Loss	-0.08			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$
–3 dB Bandwidth	90			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; Figure 25
C _s (OFF)	32			pF typ	_
C _D (OFF)	38			pF typ	
C _D , C _s (ON)	60			pF typ	
POWER REQUIREMENTS	İ				$V_{DD} = 1.95 V$
lod	0.003			μA typ	Digital inputs = 0 V or 1.95 V
		1.0	4	µA max	

Table 3. V_{DD} = 1.65 V to 1.95 V, GND = 0 V, unless otherwise noted¹

¹Temperature range for the Y version is –40°C to +125°C. ²Guaranteed by design, not subject to production test.

ABSOLUTE MAXIMUM RATINGS

Table 4. $T_A = 25^{\circ}$ C, unless otherwise noted

Parameter	Rating
V _{DD} to GND	–0.3 V to +4.6 V
Analog Inputs ¹	-0.3 V to V _{DD} + 0.3 V
Digital Inputs ¹	GND – 0.3 V to 4.6 V or 10 mA, whichever occurs first
Peak Current, S or D	(Pulsed at 1 ms, 10% Duty Cycle Max)
3.3 V Operation	500 mA
2.5 V Operation	460 mA
1.8 V Operation	420 mA
Continuous Current, S or D	
3.3 V Operation	300 mA
2.5 V Operation	275 mA
1.8 V Operation	250 mA
Operating Temperature Range Automotive (Y Version)	−40°C to +125°C
Storage Temperature Range	–65°C to +150°C
Junction Temperature	150°C
TSSOP Package	
θ_{JA} Thermal Impedance	150°C/W
θ_{JC} Thermal Impedance	27°C/W
IR Reflow, Peak Temperature <20 sec	235℃

Table 5. ADG811/ADG812 Truth Table

ADG811 IN	ADG812 IN	Switch Condition
0	1	On
1	0	Off

Table 6. ADG813 Truth Table

Logic	Switch 1, Switch 4	Switch 2, Switch 3
0	Off	On
1	On	Off

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although this product features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



¹ Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

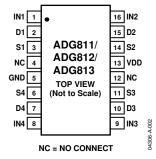




Table 7. Terminology Term Definition V_{DD} Most positive power supply potential. Positive supply current. DD GND Ground (0 V) reference. S Source terminal. May be an input or output. D Drain terminal. May be an input or output. Logic control input. IN VD, Vs Analog voltage on Terminals D, S. Ohmic resistance between D and S. Ron Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the RFLAT (ON) specified analog signal range. ΔR_{ON} On resistance match between any two channels, i.e., Ron max – Ron min. Is (OFF) Source leakage current with the switch off. I_D (OFF) Drain leakage current with the switch off. ID, Is (ON) Channel leakage current with the switch on. VINL Maximum input voltage for Logic 0. VINH Minimum input voltage for Logic 1. IINL (IINH) Input current of the digital input. Cs (OFF) Off switch source capacitance. Measured with reference to ground. C_D (OFF) Off switch drain capacitance. Measured with reference to ground. C_D, C_S (ON) On switch capacitance. Measured with reference to ground. CIN Digital input capacitance. Delay time between the 50% and the 90% points of the digital input and switch on condition. ton Delay time between the 50% and the 90% points of the digital input and switch off condition. toff tBBM On or off time measured between the 80% points of both switches, when switching from one to another. **Charge Injection** A measure of the glitch impulse transferred from the digital input to the analog output during on-to-off switching. Off Isolation A measure of unwanted signal coupling through an off switch. A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance. Crosstalk -3 dB Bandwidth The frequency at which the output is attenuated by 3 dB. On Response The frequency response of the on switch. Insertion Loss The loss due to the on resistance of the switch. THD + N The ratio of the harmonic amplitudes plus noise of a signal to the fundamental.

TYPICAL PERFORMANCE CHARACTERISTICS

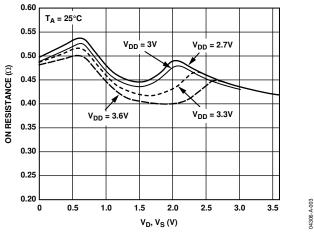


Figure 3. On Resistance vs. V_D (V_S), $V_{DD} = 2.7$ V to 3.6 V

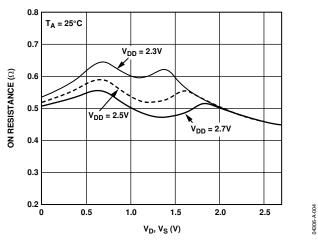


Figure 4. On Resistance vs. V_D (V_S), V_{DD} = 2.5 V ± 0.2 V

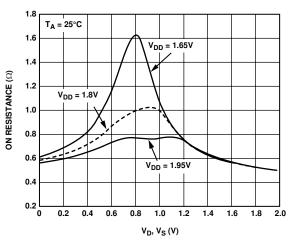


Figure 5. On Resistance vs. V_D (V_s), V_{DD} = 1.8 V \pm 0.15 V

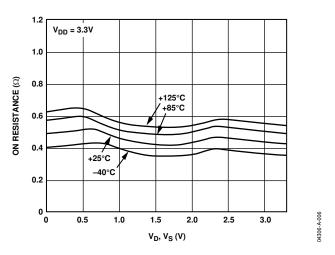
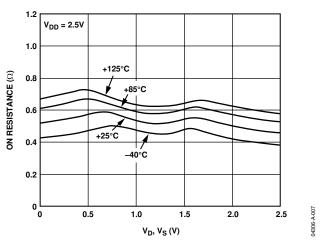
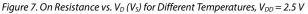


Figure 6. On Resistance vs. V_D (V_S) for Different Temperatures, $V_{DD} = 3.3 V$





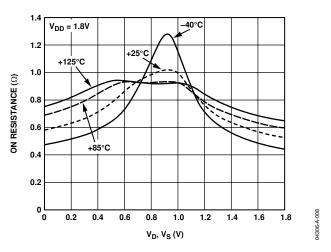


Figure 8. On Resistance vs. V_D (V_s) for Different Temperatures, $V_{DD} = 1.8 V$

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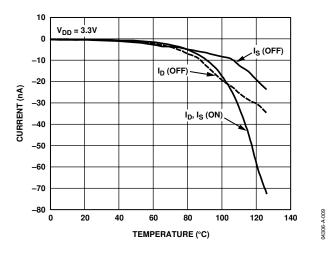


Figure 9. Leakage Currents vs. Temperature, V_{DD} = 3.3 V

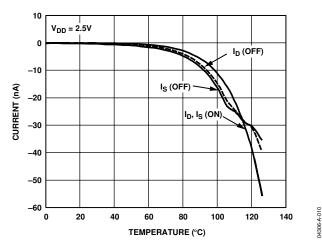


Figure 10. Leakage Currents vs. Temperature, $V_{DD} = 2.5 V$

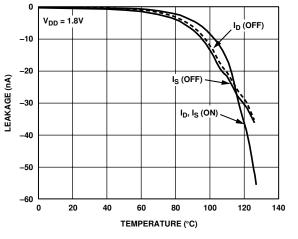


Figure 11. Leakage Currents vs. Temperature, V_{DD} = 1.8 V

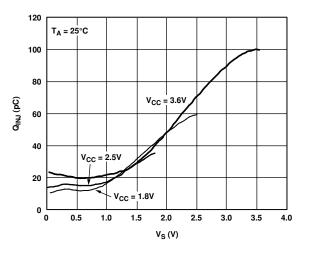
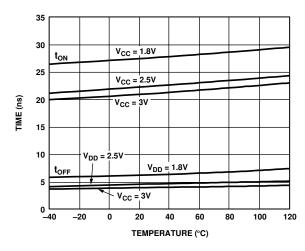
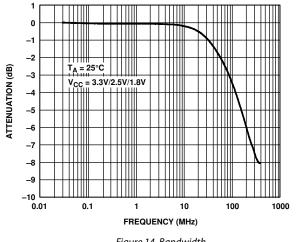


Figure 12. Charge Injection vs. Source Voltage





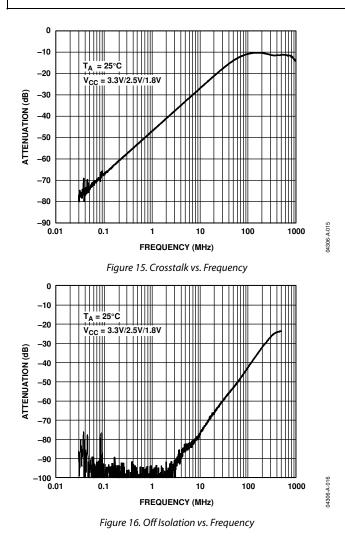




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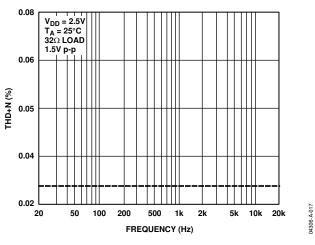
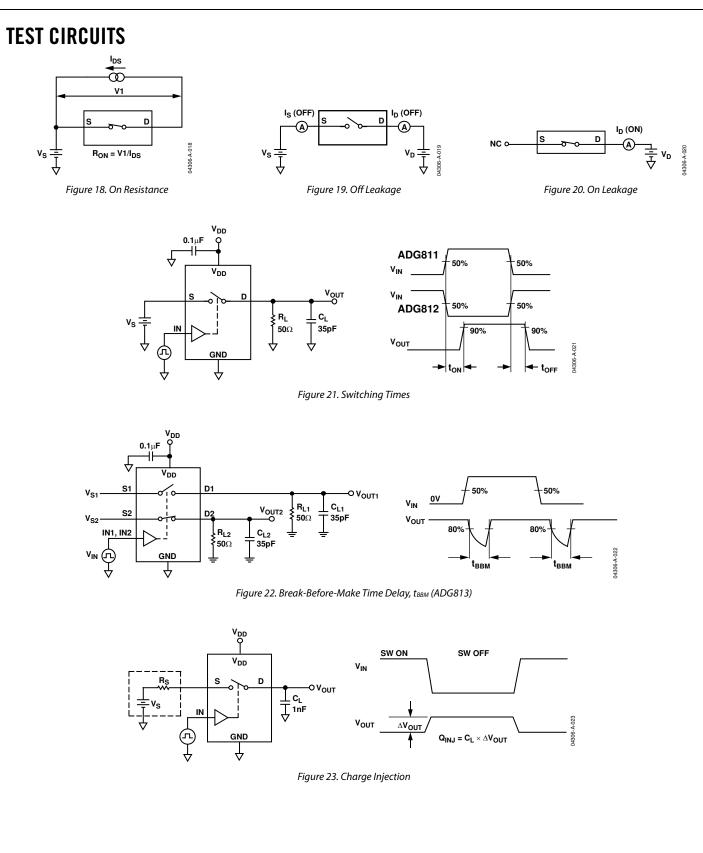


Figure 17. Total Harmonic Distortion



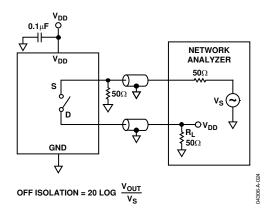


Figure 24. Off Isolation

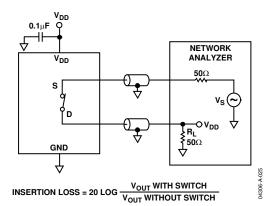


Figure 25. Bandwidth

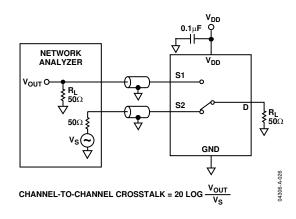


Figure 26. Channel-to-Channel Crosstalk

OUTLINE DIMENSIONS

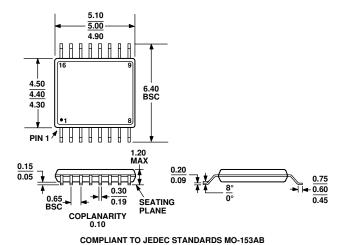


Figure 27. 16-Lead Thin Shrink Small Outline Package [TSSOP] (RU-16) Dimensions shown in millimeters

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option
ADG811YRU	–40°C to +125°C	Thin Shrink Small Outline (TSSOP)	RU-16
ADG811YRU-REEL	–40°C to +125°C	Thin Shrink Small Outline (TSSOP)	RU-16
ADG811YRU-REEL7	–40°C to +125°C	Thin Shrink Small Outline (TSSOP)	RU-16
AADG812YRU	–40°C to +125°C	Thin Shrink Small Outline (TSSOP)	RU-16
ADG812YRU-REEL	-40°C to +125°C	Thin Shrink Small Outline (TSSOP)	RU-16
ADG812YRU-REEL7	-40°C to +125°C	Thin Shrink Small Outline (TSSOP)	RU-16
ADG813YRU	–40°C to +125°C	Thin Shrink Small Outline (TSSOP)	RU-16
ADG813YRU-REEL	–40°C to +125°C	Thin Shrink Small Outline (TSSOP)	RU-16
ADG813YRU-REEL7	–40°C to +125°C	Thin Shrink Small Outline (TSSOP)	RU-16

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